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RD53 investigation of CMOS radiation hardness up to 1Grad

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This talk will review progress and status of testing of deep submicron CMOS technology for tolerance to radiation with total ionizing dose up to 1Grad, and also for tolerance to single event effects. Multiple prototypes have been fabricated and tested with x-rays, gamma rays, and protons. Devices tested range from single transistors to full circuits. A summary of results obtained so far will be presented.

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